Shinsuke Harada

List of Publications by Year
in descending order

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142	2,053	21	35
papers	citations	h-index	g-index
		331259	360668

142	142	142	1021
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Improved Channel Mobility in 4H-SiC MOSFETs by Boron Passivation. IEEE Electron Device Letters, 2014, 35, 1176-1178.	2.2	98
2	Characterization of traps at nitrided SiO₂/SiC interfaces near the conduction band edge by using Hall effect measurements. Applied Physics Express, 2017, 10, 046601.	1.1	96
3	Excellent effects of hydrogen postoxidation annealing on inversion channel mobility of 4H-SiC MOSFET fabricated on (11 2 0) face. IEEE Electron Device Letters, 2002, 23, 13-15.	2.2	94
4	Development of Ultrahigh-Voltage SiC Devices. IEEE Transactions on Electron Devices, 2015, 62, 396-404.	1.6	78
5	Relationship between channel mobility and interface state density in SiC metalâ€“oxideâ€“semiconductor field-effect transistor. Journal of Applied Physics, 2002, 91, 1568-1571.	1.1	70
6	3.3-kV-Class 4H-SiC MeV-Implanted UMOSFET With Reduced Gate Oxide Field. IEEE Electron Device Letters, 2016, 37, 314-316.	2.2	58
7	High channel mobility in normally-off 4H-SiC buried channel MOSFETs. IEEE Electron Device Letters, 2001, 22, 272-274.	2.2	54
8	Homogeneous Amorphization in High-Energy Ion Implanted Si. Physical Review Letters, 1997, 78, 2980-2982.	2.9	50
9	Evolution of threading screw dislocation conversion during solution growth of 4H-SiC. APL Materials, 2013, 1, .	2.2	50
10	Correlation between channel mobility and shallow interface traps in SiC metalâ€“oxideâ€“semiconductor field-effect transistors. Journal of Applied Physics, 2002, 92, 6230-6234.	1.1	48
11	Temperature-dependent analysis of conduction mechanism of leakage current in thermally grown oxide on 4H-SiC. Journal of Applied Physics, 2015, 117, .	1.1	48
12	Body PiN diode inactivation with low on-resistance achieved by a 1.2 kV-class 4H-SiC SWITCH-MOS. , 2017, , .		47
13	Strong dependence of the inversion mobility of 4H and 6H SiC(0001) MOSFETs on the water content in pyrogenic re-oxidation annealing. IEEE Electron Device Letters, 2002, 23, 136-138.	2.2	46
14	Interface carbon defects at 4H-SiC(0001)/SiO2 interfaces studied by electron-spin-resonance spectroscopy. Applied Physics Letters, 2018, 113, .	1.5	38
15	Evaluation of Schottky barrier height on 4H-SiC <i>m</i>-face ${ 1ar{1}00} $ for Schottky barrier diode wall integrated trench MOSFET. Japanese Journal of Applied Physics, 2017, 56, 04CR08.	0.8	33
16	Recrystallization of MeV Si implanted 6Hâ€SiC. Applied Physics Letters, 1996, 69, 3534-3536.	1.5	31
17	Determination of optimum structure of 4H-SiC Trench MOSFET. , 2012, , .		31
18	Threshold-voltage instability in 4H-SiC MOSFETs with nitrided gate oxide revealed by non-relaxation method. Japanese Journal of Applied Physics, 2016, 55, 04ER11.	0.8	28

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19	8.5-<tex>$hbox mOmega cdot hbox cm^2$</tex>600-V Double-Epitaxial MOSFETs in 4Hâ€"SiC. IEEE Electron Device Letters, 2004, 25, 292-294.	2.2	27
20	Enantioselective amplification on circularly polarized laser-induced chiral nucleation from a NaClO₃solution containing Ag nanoparticles. CrystEngComm, 2016, 18, 7441-7448.	1.3	27
21	Isotropic Channel Mobility in UMOSFETs on 4H-SiC C-Face with Vicinal Off-Angle. Materials Science Forum, 0, 645-648, 999-1004.	0.3	24
22	Single photon sources in 4H-SiC metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2018, 112, .	1.5	24
23	First Demonstration of Short-Circuit Capability for a 1.2 kV SiC SWITCH-MOS. IEEE Journal of the Electron Devices Society, 2019, 7, 613-620.	1.2	23
24	Demonstration of Superior Electrical Characteristics for 1.2 kV SiC Schottky Barrier Diode-Wall Integrated Trench MOSFET With Higher Schottky Barrier Height Metal. IEEE Electron Device Letters, 2020, 41, 1810-1813.	2.2	23
25	Amorphization and solid phase epitaxy of high-energy ion implanted 6H-SiC. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 195-197.	0.6	22
26	Ideal phonon-scattering-limited mobility in inversion channels of 4H-SiC(0001) MOSFETs with ultralow net doping concentrations. Applied Physics Letters, 2019, 115, .	1.5	22
27	Impact of crystal faces of 4H-SiC in SiO₂/4H-SiC structures on interface trap densities and mobilities. Applied Physics Express, 2019, 12, 021003.	1.1	21
28	First Demonstration of a Monolithic SiC Power IC Integrating a Vertical MOSFET with a CMOS Gate Buffer. , 2021, , .		21
29	Anomalous carbon clusters in 4H-SiC/SiO2 interfaces. Journal of Applied Physics, 2019, 125, .	1.1	20
30	Carbon dangling-bond center (carbon <i>P</i>b center) at 4H-SiC(0001)/SiO2 interface. Applied Physics Letters, 2020, 116, .	1.5	20
31	Characterization of near-interface traps at 4H-SiC metalâ€"oxideâ€"semiconductor interfaces using modified distributed circuit model. Applied Physics Express, 2017, 10, 064101.	1.1	19
32	Two-step SiC solution growth for dislocation reduction. Journal of Crystal Growth, 2017, 468, 874-878.	0.7	19
33	Electron-spin-resonance and electrically detected-magnetic-resonance characterization on <i>P</i>bC center in various 4H-SiC(0001)/SiO2 interfaces. Journal of Applied Physics, 2020, 127, .	1.1	18
34	Influence of Processing and of Material Defects on the Electrical Characteristics of SiC-SBDs and SiC-MOSFETs. Materials Science Forum, 0, 645-648, 655-660.	0.3	17
35	Self-aligned formation of the trench bottom shielding region in 4H-SiC trench gate MOSFET. Japanese Journal of Applied Physics, 2016, 55, 04ER02.	0.8	17
36	Sub-nanometer-scale depth profiling of nitrogen atoms in SiO₂/4H-SiC structures treated with NO annealing. Applied Physics Express, 2018, 11, 101303.	1.1	17

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37	High-temperature Performance of 1.2 kV-class SiC Super Junction MOSFET. , 2019, , .		17
38	Ultra-Low Specific on-Resistance Achieved in 3.3 kV-Class SiC Superjunction MOSFET. , 2021, , .		17
39	Transmission electron microscopy studies of crystal-to-amorphous transition in ion implanted silicon. Journal of Applied Physics, 1997, 81, 1126-1130.	1.1	16
40	Effect of boron incorporation on slow interface traps in SiO2/4H-SiC structures. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	1.1	16
41	Insight into enhanced field-effect mobility of 4H-SiC MOSFET with Ba incorporation studied by Hall effect measurements. AIP Advances, 2018, 8, .	0.6	16
42	Microstructural evolution of oxygen implanted silicon during annealing processes. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 311-316.	0.6	15
43	Influence of Post-Oxidation Process on the MOS Interface and MOSFETs Properties. Materials Science Forum, 2001, 353-356, 643-646.	0.3	15
44	4H-SiC Lateral RESURF MOSFET with a Buried Channel Structure. Materials Science Forum, 2003, 433-436, 753-756.	0.3	15
45	1.8 mΩcm², 10 A Power MOSFET in 4H-SiC. , 2006, , .		15
46	Improvement of Channel Mobility in 4H-SiC C-Face MOSFETs by H₂ Rich Wet Re-Oxidation. Materials Science Forum, 0, 778-780, 975-978.	0.3	15
47	Threshold Voltage Instability of SiC-MOSFETs on Various Crystal Faces. Materials Science Forum, 0, 778-780, 521-524.	0.3	15
48	Reduction of interface states by hydrogen treatment at the aluminum oxide/4H-SiC Si-face interface. AIP Advances, 2016, 6, .	0.6	15
49	Role of Trench Bottom Shielding Region on Switching Characteristics of 4H-SiC Double-Trench Mosfets. Materials Science Forum, 0, 924, 748-751.	0.3	14
50	Evaluation of a SiC power module using low-on-resistance IEMOSFET and JBS for high power density power converters. , 2010, , .		13
51	(Invited) SiC MOS Interface States: Difference between Si Face and C Face. ECS Transactions, 2013, 58, 55-60.	0.3	13
52	Dynamic characteristics of large current capacity module using 16-kV ultrahigh voltage SiC flip-type n-channel IE-IGBT. , 2014, , .		13
53	Evaluation of silicon- and carbon-face SiO2/SiC MOS interface quality based on scanning nonlinear dielectric microscopy. Applied Physics Letters, 2017, 111, .	1.5	13
54	Improved Channel Mobility in Normally-Off 4H-SiC MOSFETs with Buried Channel Structure. Materials Science Forum, 2002, 389-393, 1069-1072.	0.3	12

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55	Improvements in Electrical Properties of n-Type-Implanted 4H-SiC Substrates Using High-Temperature Rapid Thermal Annealing. Materials Science Forum, 2002, 389-393, 795-798.	0.3	12
56	Systematic investigation on in-plane anisotropy of surface and buried channel mobility of metal-oxide-semiconductor field-effect-transistors on Si-, a-, and m-face 4H-SiC. Applied Physics Letters, 2015, 106, .	1.5	12
57	Impact of oxide thickness on the density distribution of near-interface traps in 4H-SiC MOS capacitors. Japanese Journal of Applied Physics, 2018, 57, 06KA04.	0.8	12
58	Significant Improvement of Inversion Channel Mobility in 4H-SiC MOSFET on (11-20) Face Using Hydrogen Post-Oxidation Annealing. Materials Science Forum, 2002, 389-393, 1061-1064.	0.3	11
59	Study on advanced power device performance under real circuit conditions with an exact power loss simulator. , 2007, , .		11
60	3.3 kV-Class 4H-SiC UMOSFET by Double-Trench with Tilt Angle Ion Implantation. Materials Science Forum, 2016, 858, 974-977.	0.3	11
61	Difference in electron mobility at 4Hâ€“SiC/SiO2 interfaces with various crystal faces originating from effective-field-dependent scattering. Applied Physics Letters, 2020, 117, .	1.5	11
62	Effects of Pyrogenic Reoxidation Annealing on Inversion Channel Mobility of 4H-SiC Metal-Oxide-Semiconductor Field-Effect Transistor Fabricated on $(11ar{2}0)$ Face. Japanese Journal of Applied Physics, 2001, 40, L1201-L1203.	0.8	10
63	4.3 mÎ©cm², 1100 V 4H-SiC Implantation and Epitaxial MOSFET. Materials Science Forum, 2006, 527-529, 1281-1284.	0.3	10
64	Exact Characterization of Threshold Voltage Instability in 4H-SiC MOSFETs by Non-Relaxation Method. Materials Science Forum, 0, 821-823, 685-688.	0.3	10
65	Accurate evaluation of fast threshold voltage shift for SiC MOS devices under various gate bias stress conditions. Japanese Journal of Applied Physics, 2018, 57, 04FA07.	0.8	10
66	Electrically detected magnetic resonance study on interface defects at nitrided Si-face, <i>a</i>-face, and <i>m</i>-face 4H-SiC/SiO2 interfaces. Applied Physics Letters, 2020, 116, .	1.5	10
67	Comprehensive Study on Electrical Characteristics in 1.2 kV SiC SBD-integrated Trench and Planar MOSFETs. , 2021, , .		10
68	Low on-resistance in inversion channel IEMOSFET formed on 4H-SiC C-face substrate. , 0, , .		8
69	High Inversion Channel Mobility of 4H-SiC MOSFETs Fabricated on C(000-1) Epitaxial Substrate with Vicinal (Below 1Âº) Off-Angle. Materials Science Forum, 2006, 527-529, 1043-1046.	0.3	8
70	Influence of Metallization Annealing on Channel Mobility in 4H-SiC MOSFET on Carbon Face. Materials Science Forum, 0, 600-603, 675-678.	0.3	8
71	High Performance SiC IEMOSFET/SBD Module. Materials Science Forum, 2012, 717-720, 1053-1058.	0.3	8
72	Local deep level transient spectroscopy using super-higher-order scanning nonlinear dielectric microscopy. Microelectronics Reliability, 2016, 64, 566-569.	0.9	8

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73	Hole trapping in SiC-MOS devices evaluated by fast-capacitanceâ€“voltage method. Japanese Journal of Applied Physics, 2018, 57, 04FR15.	0.8	8
74	Electrically detected-magnetic-resonance identifications of defects at 4H-SiC(000 1 Â¯)/SiO2 interfaces with wet oxidation. Applied Physics Letters, 2019, 115, 151602.	1.5	8
75	V-groove trench gate SiC MOSFET with a double reduced surface field junction termination extensions structure. Japanese Journal of Applied Physics, 2019, 58, SBBD11.	0.8	8
76	Analysis of 1.2 kV SiC SWITCH-MOS after Short-circuit Stress. , 2020, , .		8
77	Highly Efficient Switching Operation of 1.2 kV-Class SiC SWITCH-MOS. Materials Science Forum, 0, 1004, 795-800.	0.3	8
78	Demonstration of motor drive with SiC normally-off IBMOSFET/SBD power converter. , 2007, , .		7
79	Dynamic Characterization of the Threshold Voltage Instability under the Pulsed Gate Bias Stress in 4H-SiC MOSFET. Materials Science Forum, 0, 897, 549-552.	0.3	7
80	Analysis of fast and slow responses in AC conductance curves for p-type SiC MOS capacitors. Japanese Journal of Applied Physics, 2018, 57, 06KA06.	0.8	7
81	Mobility-limiting Coulomb scattering in nitrided 4H-SiC inversion channel on 1 1 Â¯ 00 m-face and 11 2 Â¯ 0 a-face characterized by Hall effect measurements. Applied Physics Letters, 2019, 115, 132106.	1.5	7
82	Demonstration and analysis of channel mobility, trapped electron density and Hall effect at SiO₂/SiC (0$ar{3}$3$ar{8}$) interfaces. Japanese Journal of Applied Physics, 2019, 58, SBBD04.	0.8	7
83	Demonstration of the Surge Current Capability of Embedded SBDs in SiC SBD-Integrated Trench MOSFETs with a Thick Cu Block. , 2022, , .		7
84	Recrystallization and electrical properties of MeV P implanted 6Hâ€“SiC. Journal of Applied Physics, 2000, 87, 2655-2657.	1.1	6
85	A Large Reduction in Interface-State Density for MOS Capacitor on 4H-SiC (11-2 0) Face Using H₂ and H₂O Vapor Atmosphere Post-Oxidation Annealing. Materials Science Forum, 2002, 389-393, 1057-1060.	0.3	6
86	(Invited) SiC MOS Interface States: Similarity and Dissimilarity from Silicon. ECS Transactions, 2013, 50, 305-311.	0.3	6
87	Electrical Properties of MOS Structures on 4H-SiC (11-20) Face. Materials Science Forum, 2013, 740-742, 621-624.	0.3	6
88	13-kV, 20-A 4H-SiC PiN Diodes for Power System Applications. Materials Science Forum, 2014, 778-780, 855-858.	0.3	6
89	(Invited) Interface Defects in C-face 4H-SiC MOSFETs: An Electrically-Detected-Magnetic-Resonance Study. ECS Transactions, 2017, 80, 147-153.	0.3	6
90	Nitridation Effects of Gate Oxide on Channel Properties of SiC Trench MOSFETs. Materials Science Forum, 2014, 778-780, 615-618.	0.3	5

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91	Edge Termination Design with Strong Process Robustness for 1.2 kV-class 4H-SiC Super Junction V-groove MOSFETs. , 2020, , .		5
92	Electrical detection of TV2a-type silicon vacancy spin defect in 4H-SiC MOSFETs. Applied Physics Letters, 2022, 120, 064001.	1.5	5
93	Analysis of Low On-Resistance in 4H-SiC Double-Epitaxial MOSFET. Materials Science Forum, 2005, 483-485, 813-816.	0.3	4
94	Comparative Study of Characteristics of Lateral MOSFETs Fabricated on 4H-SiC (11-20) and (1-100) Faces. Materials Science Forum, 2015, 821-823, 721-724.	0.3	4
95	Progress in High and Ultrahigh Voltage Silicon Carbide Device Technology. , 2018, , .		4
96	Conduction mechanisms of oxide leakage current in p-channel 4H-SiC MOSFETs. Japanese Journal of Applied Physics, 2020, 59, 044003.	0.8	4
97	Experimental and Numerical Demonstration of Superior RBSOAs in 1.2 kV SiC Trench and SBD-integrated Trench MOSFETs. , 2021, , .		4
98	Correlation between Inversion Channel Mobility and Interface Traps near the Conduction Band in SiC MOSFETs. Materials Science Forum, 2002, 389-393, 1045-1048.	0.3	3
99	High Temperature Ion Implantation and Activation Annealing Technologies for Mass Production of SiC Power Devices. Materials Science Forum, 0, 717-720, 821-824.	0.3	3
100	Reliability Improvement and Optimization of Trench Orientation of 4H-SiC Trench-Gate Oxide. Materials Science Forum, 2014, 778-780, 537-540.	0.3	3
101	Low R_{ons} in 3kV 4H-SiC UMOSFET with MeV Implanted Buried P-Base Region. Materials Science Forum, 2015, 821-823, 769-772.	0.3	3
102	An experimental study on dynamic junction temperature estimation of SiC MOSFET with built-in SBD. IEICE Electronics Express, 2019, 16, 20190392-20190392.	0.3	3
103	High-Temperature Operating Characteristics of Inverter Using SBD-Integrated MOSFET. Materials Science Forum, 0, 1004, 1115-1122.	0.3	3
104	A New JTE Technique for Vertical GaN Power Devices by Conductivity Control Using Boron Implantation into p-Type Layer. , 2021, , .		3
105	Crystal-orientation-dependent flatband voltage of non-polar GaN MOS interfaces investigated using trench sidewall capacitors. Applied Physics Letters, 2021, 119, .	1.5	3
106	Dipole scattering at the interface: The origin of low mobility observed in SiC MOSFETs. Journal of Applied Physics, 2022, 131, .	1.1	3
107	Examination of compound formation at interface of tin-bismuth-silver solder and copper substrate by using electron probe micro analysis. X-Ray Spectrometry, 2002, 31, 3-6.	0.9	2
108	Fabrication of 4H-SiC Double-Epitaxial MOSFETs. Materials Science Forum, 2004, 457-460, 1421-1424.	0.3	2

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109	Activation Treatment of Ion Implanted Dopants Using Hybrid Super RTA Equipment. Materials Science Forum, 2006, 527-529, 803-806.	0.3	2
110	4.3 m.OMEGA.cm2, 1100 V normally-off IEMOSFET on SiC. IEEJ Transactions on Industry Applications, 2007, 127, 267-272.	0.1	2
111	1360 V, 5.0 mÎ©cm² Double-Implanted MOSFETs Fabricated on 4H-SiC(000-1). Materials Science Forum, 2010, 645-648, 987-990.	0.3	2
112	Ultrahigh voltage SiC bipolar devices. , 2013, , .		2
113	Development of ultrahigh voltage SiC power devices. , 2014, , .		2
114	C-Face Interface Defects in 4H-SiC MOSFETs Studied by Electrically Detected Magnetic Resonance. Materials Science Forum, 2014, 778-780, 414-417.	0.3	2
115	Oxidation-Process Dependence of Single Photon Sources Embedded in 4H-SiC MOSFETs. Materials Science Forum, 0, 924, 281-284.	0.3	2
116	Sub-nm-Scale Depth Profiling of Nitrogen in NO- and N₂-Annealed SiO₂/4H-SiC(0001) Structures. Materials Science Forum, 0, 963, 226-229.	0.3	2
117	The Effect of Î³-Ray Irradiation on Optical Properties of Single Photon Sources in 4H-SiC MOSFET. Materials Science Forum, 0, 1004, 361-366.	0.3	2
118	Free carrier density enhancement of 4H-SiC Si-face MOSFET by Ba diffusion process and NO passivation. Japanese Journal of Applied Physics, 2021, 60, SBBD08.	0.8	2
119	Accurate determination of threshold voltage shift during negative gate bias stress in 4H-SiC MOSFETs by fast on-the-fly method. Japanese Journal of Applied Physics, 2021, 60, 060901.	0.8	2
120	Evaluation of drain current decrease by AC gate bias stress in commercially available SiC MOSFETs. , 2017, , .		2
121	Iron loss evaluation of magnetic materials excited by a SiC inverter with a Schottky barrier diode wall-integrated trench MOSFET. AIP Advances, 2020, 10, 125129.	0.6	2
122	1.2 kV GaN/SiC-based Hybrid High Electron Mobility Transistor with Non-destructive Breakdown. , 2021, , .		2
123	Enhanced Short-circuit Capability for 1.2 kV SiC SBD-integrated Trench MOSFETs Using Cu Blocks Sintered on the Source Pad. , 2022, , .		2
124	Comparative Study of Performance of SiC SJ-MOSFETs Formed by Multi-epitaxial Growth and Trench-filling Epitaxial Growth. , 2022, , .		2
125	Wafer-scale Fabrication of Vertical GaN p-n Diodes with Graded JTE Structures Using Multiple-zone Boron Implantation. , 2022, , .		2
126	Carbonization of SIMOX Substrates for Fabrication of Single-crystal SiC-on-insulator. Materials Science Forum, 2000, 338-342, 297-300.	0.3	1

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127	Influence of the Crystalline Quality of Epitaxial Layers on Inversion Channel Mobility in 4H-SiC MOSFETs. Materials Science Forum, 2002, 389-393, 1053-1056.	0.3	1
128	TCAD Optimisation of 4H-SiC Channel-Doped MOSFET with P-Polysilicon Gate. Materials Science Forum, 2002, 389-393, 1085-1088.	0.3	1
129	Activation of p-Type Dopants in 4Hâ€"SiC Using Hybrid Super-Rapid Thermal Annealing Equipment. Japanese Journal of Applied Physics, 2007, 46, 5342-5344.	0.8	1
130	Positron Trapping Sites Originating from Oxide Interfaces on 4H-SiC C(000ar1)- and Si(0001)-Faces. Japanese Journal of Applied Physics, 2008, 47, 8391-8393.	0.8	1
131	Impact of Carbon Cap Annealing on Gate Oxide Reliability on 4H-SiC (000-1) C-Face. Materials Science Forum, 0, 615-617, 549-552.	0.3	1
132	1.4kV Double-Implanted MOSFETs Fabricated on 4H-SiC(000-1). Materials Science Forum, 0, 679-680, 607-612.	0.3	1
133	Conduction Mechanism of Leakage Current in Thermal Oxide on 4H-SiC. Materials Science Forum, 2014, 778-780, 579-582.	0.3	1
134	Proposal of local deep level transient spectroscopy using super-higher-order scanning nonlinear dielectric microscopy and 2-dimensional imaging of trap distribution in SiO<inf>2</inf>/SiC interface. , 2016, , .		1
135	Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. ECS Journal of Solid State Science and Technology, 2017, 6, P547-P552.	0.9	1
136	Investigation of dVDS/dt Controllability on Rg in SWITCH-MOS to Achieve Superior Turn-on Characteristics with Low dVDS/dt. , 2020, , .		1
137	Channel Engineering of Buried-Channel 4H-SiC MOSFET Based on the Mobility Model of the Oxide/4H-SiC Interface. Materials Science Forum, 2002, 389-393, 1081-1084.	0.3	0
138	Influence of the Wet Re-Oxidation Procedure on Inversion Mobility of 4H-SiC MOSFETs. Materials Science Forum, 2002, 389-393, 1049-1052.	0.3	0
139	A 4.3â^'mÎ©cm2, 1100-V normally-off IEMOSFET on SiC. Electronics and Communications in Japan, 2008, 91, 9-14.	0.3	0
140	Challenges of 4H-SiC MOSFETs on the C(000-1) Face toward the Achievement of Ultra Low On-Resistance. Materials Science Forum, 0, 600-603, 907-912.	0.3	0
141	Effect of Ion Implantation-Induced Defects on Leakage Current Characteristics of IEMOS. Materials Science Forum, 0, 924, 353-356.	0.3	0
142	Effect of Gate Pad Layout on Thermal Impedance of SiC-MOSFET. , 2022, , .		0